

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Previously Presented) A surface emitting semiconductor laser chip, comprising:  
a semiconductor body having a radiation exit face,  
a crystal structure having principal crystal directions extending along a lateral direction of the radiation exit face, and  
side faces laterally delimiting said semiconductor body, at least one of said side faces disposed obliquely with respect to said principal crystal directions and perpendicularly with respect to said radiation exit face.
2. (Original) The semiconductor laser chip according to claim 1, wherein said semiconductor body has a cross section selected from the group of square cross sections and rectangular cross sections disposed parallel to said radiation exit face.
3. (Previously Presented) The semiconductor laser chip according to claim 1, wherein at least one of said principal crystal directions extends parallel to said radiation exit face, and at least one of said side faces forms an angle of between 40° and 50° with said at least one principal crystal direction.
4. (Original) The semiconductor laser chip according to claim 1, wherein said semiconductor body contains a substrate having, at least partly, a crystal structure.

5. (Original) The semiconductor laser chip according to claim 4, wherein said semiconductor body contains a III-V compound semiconductor.

6. (Original) The semiconductor laser chip according to claim 1, wherein the semiconductor laser chip is a VCSEL.

7. (Original) The semiconductor laser chip according to claim 3, wherein said angle is 45°.

8. (Original) The semiconductor laser chip according to claim 5, wherein said III-V compound semiconductor is selected from the group consisting of GaAs, AlGaAs, and a nitride compound semiconductor.

9. (Previously Presented) The semiconductor laser chip according to claim 3, wherein said at least one principal crystal direction is a direction.

10. (Withdrawn) A method for producing a surface emitting semiconductor laser chip, which comprises the steps of:

producing a semiconductor wafer having a plurality of surface emitting semiconductor structures, the semiconductor wafer having principal crystal directions; and

dividing the semiconductor wafer into a plurality of semiconductor laser chips along separating line, the separating lines being disposed obliquely with respect to the principal crystal

directions, each semiconductor laser chip having a radiation exit face and side faces laterally delimiting the semiconductor body, at least one of the side faces disposed obliquely with respect to the principal crystal directions and perpendicularly with respect to the radiation exit face.

11. (Withdrawn) The method according to claim 10, which further comprises performing the dividing step by one of sawing and etching the semiconductor wafer along the separating lines.

12. (Withdrawn) The method according to claim 10, which further comprises creating the separating lines to form an angle of between  $40^\circ$  and  $50^\circ$  with the principal crystal directions.

13. (Withdrawn) The method according to claim 10, which further comprises creating the separating lines to form an angle of  $45^\circ$  with the principal crystal directions.

14. (Withdrawn) The method according to claim 10, which further comprises forming the semiconductor laser chips as vertical cavity surface emitting lasers.

15. (Currently Amended) A surface emitting semiconductor laser chip, comprising: a semiconductor body having a radiation exit face, a crystal structure having principal crystal directions extending along a lateral direction of the radiation exit face, and side faces laterally delimiting said semiconductor body, at least one of said side faces disposed obliquely with respect to said principal crystal directions, and wherein ~~at least one of said principal crystal directions extends parallel to said radiation exit face and~~ to end at least one of said side faces forms an angle of

between 40° and 50° with said at least one principal crystal direction within a plane running parallel to the radiation exit face.